

# Supporting information

## From LUVs to GUVs - how to cover micrometer-sized pores with membranes

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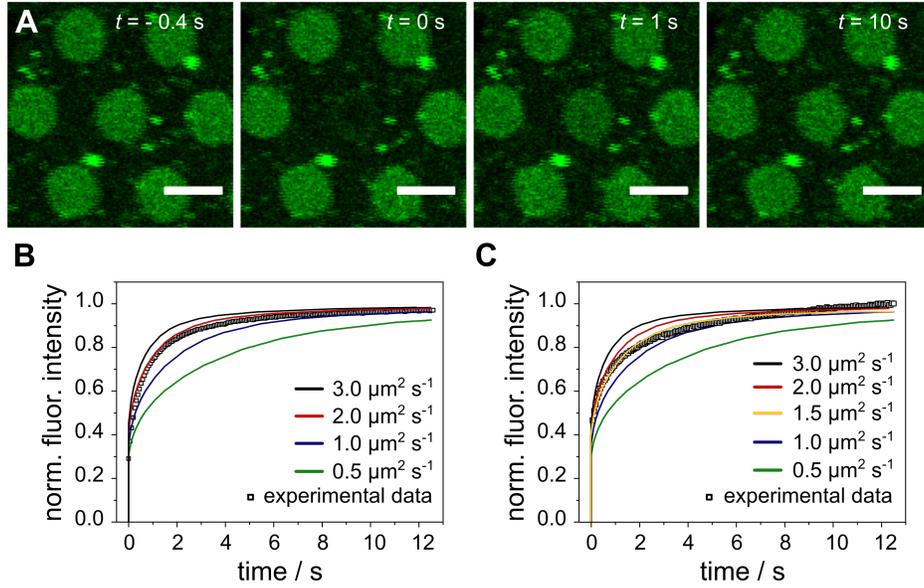


Figure 1: Indirect FRAP experiment and FEM simulations for the determination of the lipid diffusion coefficient of the s-PSM. (A) Exemplary fluorescence micrographs of an indirect FRAP experiment. Fluorescence intensity was bleached in a ROI ( $r_n = 2.2\text{-}2.3 \mu\text{m}$ ) on top of an entire f-PSM and the fluorescence recovery was observed over time. Scale bar:  $5 \mu\text{m}$ . Normalized, averaged fluorescence recovery curves of indirect FRAP experiments of the s-PSM on (C) Au/6MH and  $\text{SiO}_{1 \leq x \leq 2}$  coated substrates. Simulated recovery curves were modeled for  $D_{\text{f-PSM, sim}} = 13 \mu\text{m}^2 \text{s}^{-1}$  and different  $D_{\text{s-PSM, sim}} = 0.5\text{-}3 \mu\text{m}^2 \text{s}^{-1}$ . Lipid diffusion coefficients of the s-PSM on Au/6MH functionalized substrates of  $D_{\text{s-PSM, Au}} = 2 \mu\text{m}^2 \text{s}^{-1}$  and on  $\text{SiO}_{1 \leq x \leq 2}$  coated substrates  $D_{\text{s-PSM, SiO}} = 1.5 \mu\text{m}^2 \text{s}^{-1}$  agreed best with the experimental data.

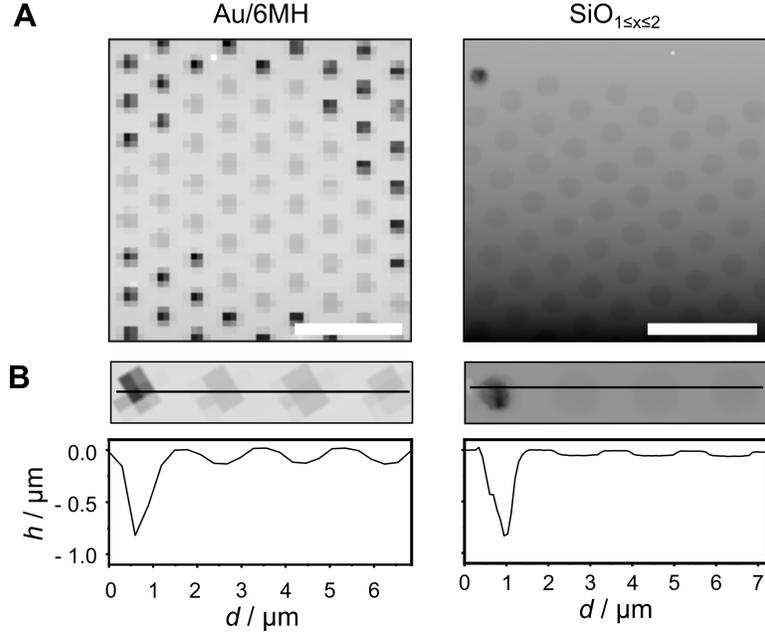


Figure 2: (A) Atomic force micrographs of PSMs prepared by spreading electroformed GUVs on porous substrates ( $d_{\text{pore}} = 1.2 \mu\text{m}$ ) functionalized with Au/6MH or SiO<sub>1≤x≤2</sub>. Scale bars: 5 μm. (B) Atomic force micrographs and corresponding height profiles along the black solid line.

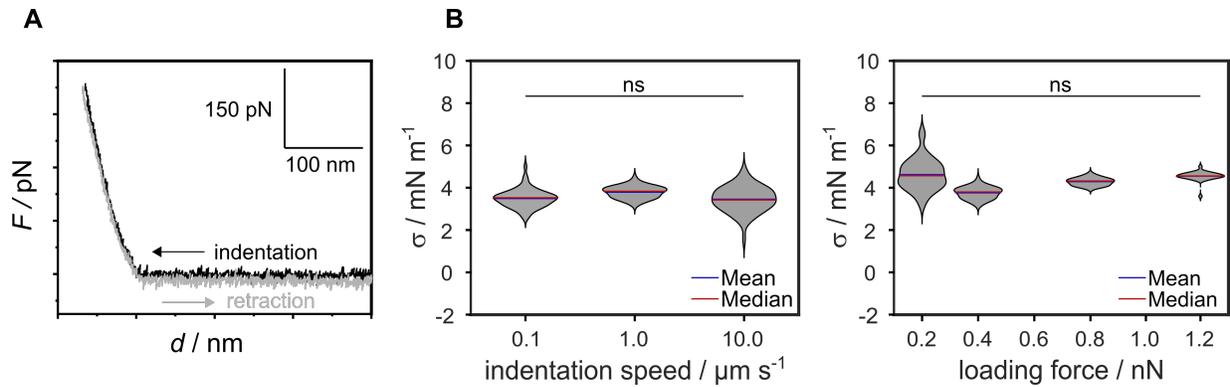


Figure 3: (A) Exemplary force-displacement curve measured in the center of an f-PSM. Influence of (B) indentation speed and (C) loading force on the lateral membrane tension. Force-displacement curves were obtained from PSMs derived from microfluidic GUVs on SiO<sub>1≤x≤2</sub> functionalized substrates (B) at different indentation speeds ( $n_{\text{all}} = 62$ ) and (C) loading forces ( $n_{0.2} = 85$ ,  $n_{0.4} = 62$ ,  $n_{0.8} = 30$ ,  $n_{1.2} = 32$ ). Statistical t-test:  $p > 0.05$  (ns).

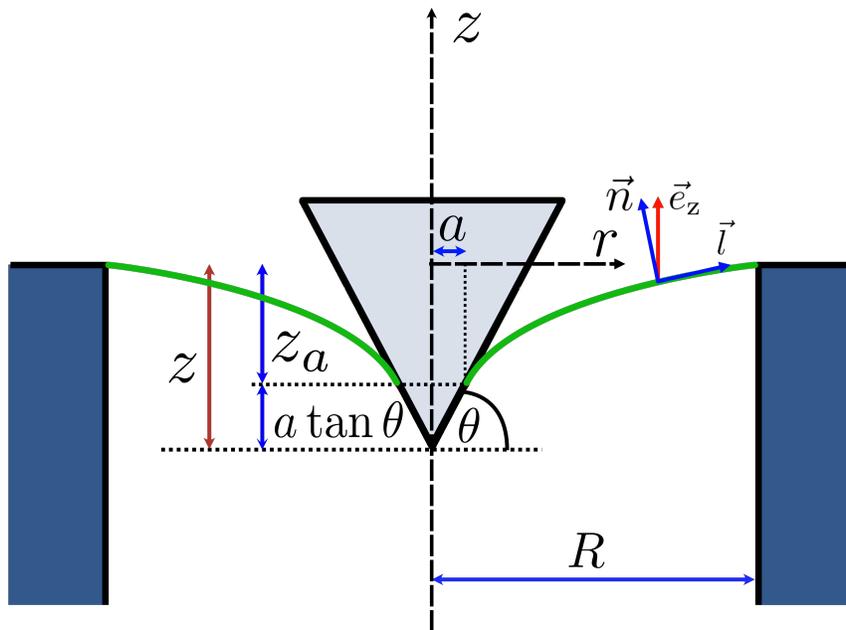


Figure 4: Parametrization of a pore-spanning membrane that is indented with a conical indenter. The symmetry is centrosymmetric. The pore edges (dark blue) act as a hinge to fix the biased membrane (green), which forms a catenoid to minimize the area or free energy.  $a$  denotes the contact radius of the membrane with the indenter, while  $z$  is the total depth of indentation.  $\theta$  is the contact angle with the indenter, while  $90 - \theta$  is half the angle of the cone.